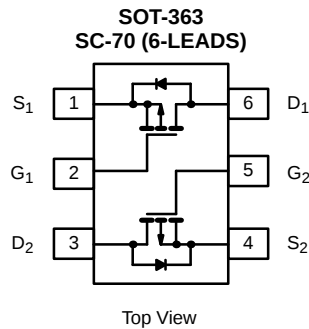


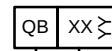


Dual P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-8	0.600 @ $V_{GS} = -4.5$ V	± 0.60
	0.850 @ $V_{GS} = -2.5$ V	± 0.50
	1.200 @ $V_{GS} = -1.8$ V	± 0.42

TrenchFET[®]
Power MOSFETs
1.8-V Rated

Marking Code

Lot Traceability
and Date Code

Part # Code

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	5 secs	Steady State
Drain-Source Voltage		V_{DS}	-8	
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	± 0.60	± 0.57
	$T_A = 85^\circ\text{C}$		± 0.43	± 0.41
Pulsed Drain Current		I_{DM}	± 1.0	
Continuous Diode Current (Diode Conduction) ^a		I_S	-0.25	-0.23
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	0.30	0.27
	$T_A = 85^\circ\text{C}$		0.16	0.14
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Typical	Maximum
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	360	415
	Steady State		400	460
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	300	350

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

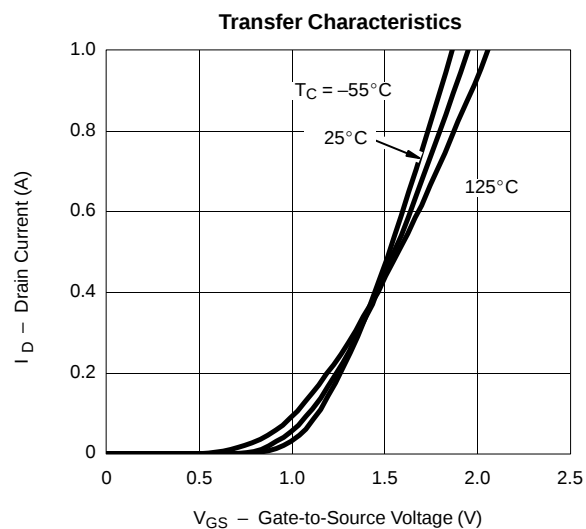
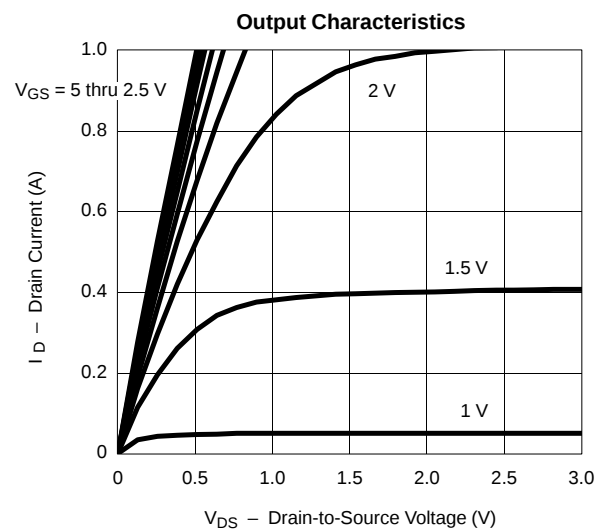
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

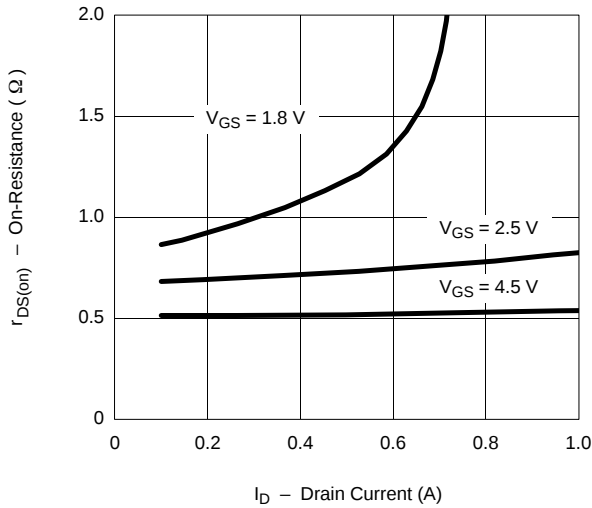
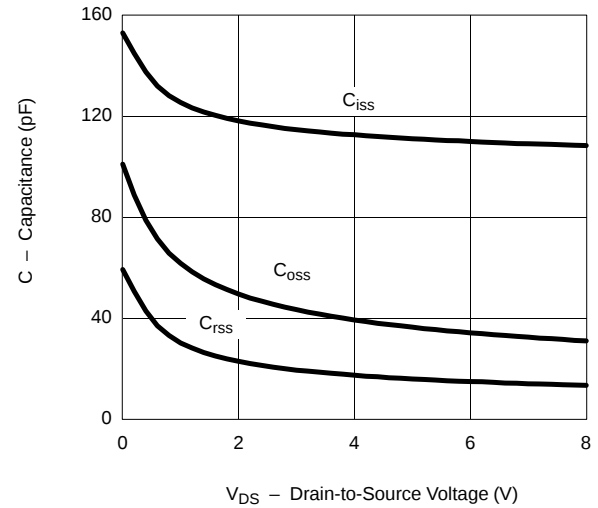
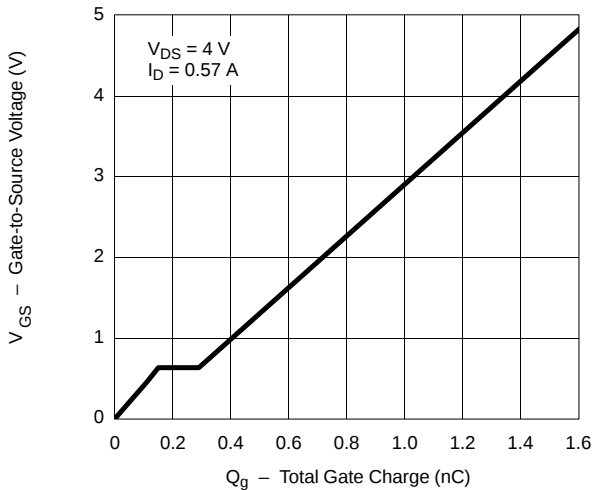
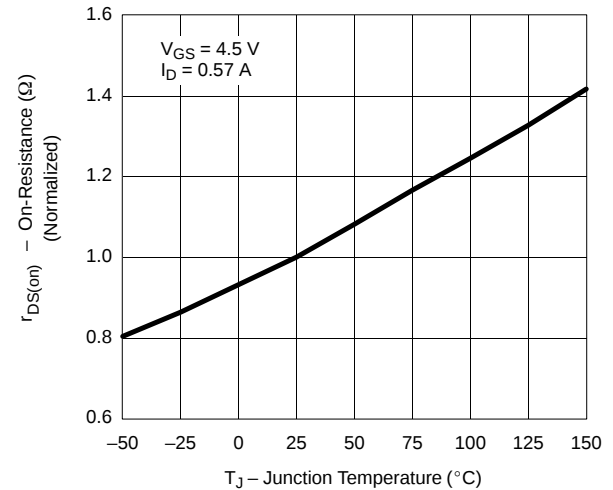
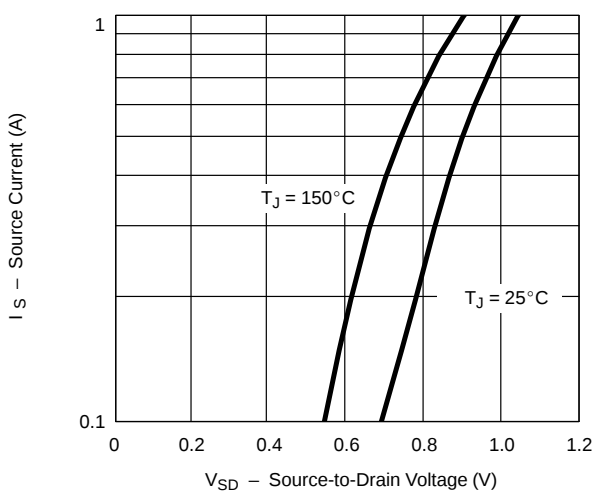
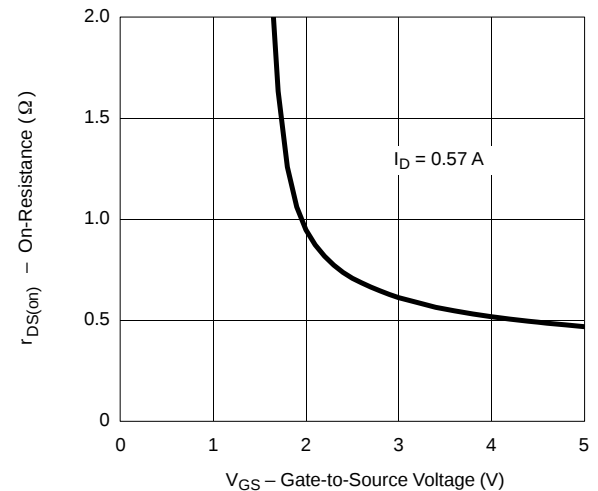
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	-0.45			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 8\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -6.4\ \text{V}$, $V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -6.4\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 85^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\ \text{V}$, $V_{GS} = -4.5\ \text{V}$	-1.0			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}$, $I_D = -0.57\ \text{A}$		0.51	0.600	Ω
		$V_{GS} = -2.5\ \text{V}$, $I_D = -0.48\ \text{A}$		0.720	0.850	
		$V_{GS} = -1.8\ \text{V}$, $I_D = -0.20\ \text{A}$		1.0	1.200	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}$, $I_D = -0.57\ \text{A}$		1.2		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.23\ \text{A}$, $V_{GS} = 0\ \text{V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -4\ \text{V}$, $V_{GS} = -4.5\ \text{V}$, $I_D = -0.57\ \text{A}$		1.5	2.3	nC
Gate-Source Charge	Q_{gs}			0.17		
Gate-Drain Charge	Q_{gd}			0.16		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\ \text{V}$, $R_L = 8\ \Omega$ $I_D \approx -0.5\ \text{A}$, $V_{GEN} = -4.5\ \text{V}$, $R_G = 6\ \Omega$		6	12	ns
Rise Time	t_r			25	50	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -0.23\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		20	40	

Notes

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage**

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)
